3PA-TCT in SiC



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- -Three-Photon-Absortion basics
- Experimental set-up for 3PA-TCT in SiC
- DUT description
- Experimental evidence of 3PA-TCT in SiC
- –Validation in non-irradiated and neutron-irradiated p-in-n diodes
- -Summary

# 3PA process basics



 Three-photon absorption (3PA) is a nonlinear optical process where a material simultaneously absorbs three photons, collectively providing enough energy to transition an electron from a lower to a higher energy state.

$$rac{dI}{dz'} = -lpha I - eta I^2 - \gamma I^3$$

– the attenuation of light intensity (I) as it propagates through a medium (z'), where  $\alpha$  is the linear absorption coefficient,  $\beta$  is the two-photon absorption (TPA) coefficient, and  $\gamma$  is the three-photon absorption (3PA) coefficient.

# 3PA in SiC: Experimental Arrangement





S: Shutter A1: Attenuator M: Mirrors A2: Attenuator

Ref.: Laser power reference L: focusing lens DUT: Device under test



Although the wavelength has doubled, a similar spatial resolution is achieved with a smaller fraction of the signal present in the profile's foot regions

#### Simpler experimental setup: using the femtosecond laser primary wavelength

Two-Photon Absorption (TPA): 42.7±3.342.7±3.3 pJ (400 nm)

Three-Photon Absorption (3PA): 481.3±3.8481.3±3.8 pJ (800 nm)

### - VERY MODERATE energy per pulse

# 3PA in SiC: DUT description

- CNM SiC planar pad diodes P in N
- Neutron-irradiated (ATI Vienna)
- Samples (non metallized contact):
  - IMW2 (Non-irradiated)

  - F2W1 (1e15 n<sub>eq</sub>/cm<sup>2</sup>)
    K6W1 (5e14 n<sub>eq</sub>/cm<sup>2</sup>)







Signal collection ring

### 3PA in SiC: Pulse temporal profile

Interferometric autocorrelation in collinear configuration

Input







# Much reduced pulse duration due to small wavelegth dispersion

### 3PA in SiC: Power scan and Z-Scan of fresh diodes





### Excellent cubic depence between the signal strengh and the laser intensity



### Z-scan dependece with bias voltaje as expected

#### 3PA-TCT for SiC, I.Vila, 2st DRD3 workshop, CERN, December 3th 2024 7

## 3PA-TCT: Irradiated SiC



 Relative suppression of the SPA contribution with respect to the TPA contribution









- First demonstration of the 3PA-TCT in SiC.
- Moderate pulse energy enables the development of compact, fiber-based, table-top 3PA-TCT systems suitable for testing wideband semiconductors.
- Shorter pulse duration: suppression of SPA background.
- Other significant advantages:
  - \_ Much simpler experimental setup.
  - \_ A more friendly wavelength for optical components.



# THANKS A LOT FOR YOUR ATTENTION

Required AI-generated and HI-edited image for the closing slide that any decent talk should have these days

